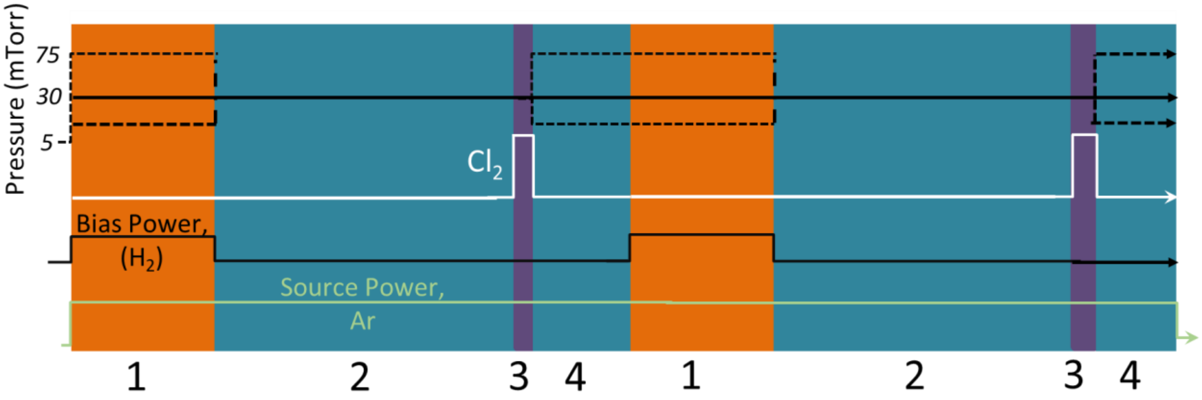

Fig 1. Graphical depiction of PE-ALE process. A 200W, 200 sccm Ar plasma is maintained throughout, with injections of 100 sccm of H_2 (1) and Cl_2 (3) separated by purge steps (2) and (4). Bias power is applied only in step (1).

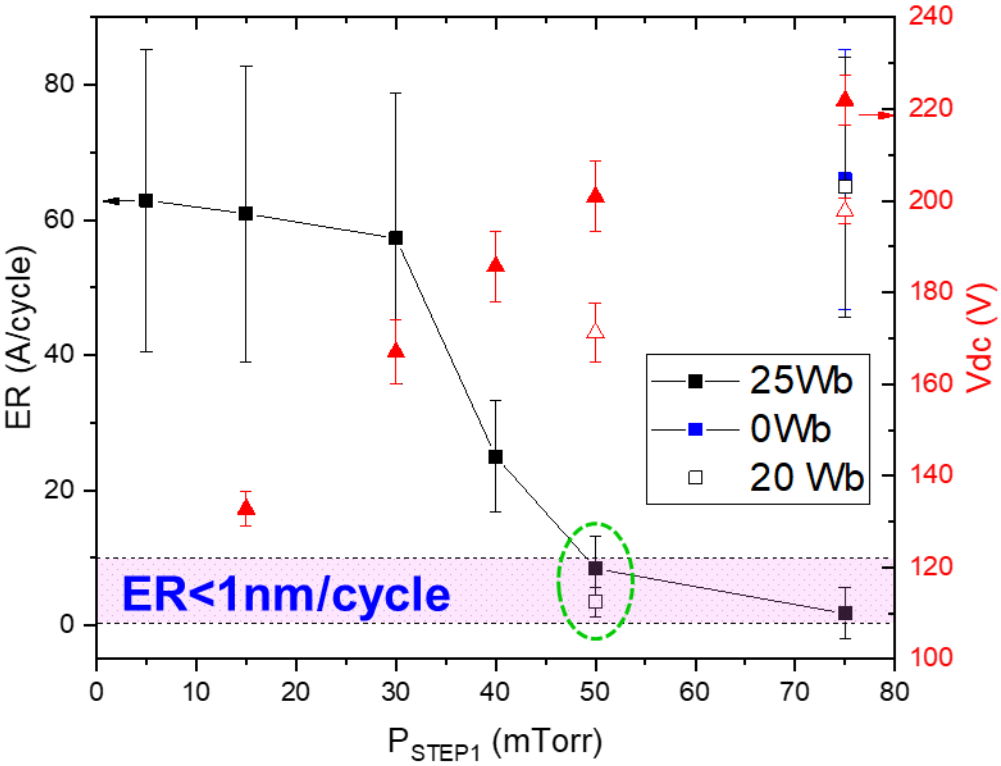

Fig 2. Etch rate of TiN as a function of Step (1) pressure in the PE-ALE process. All values for 25 W bias power unless noted. V_{DC} measurements from Step (1) are plotted on the right y-axis as triangles.